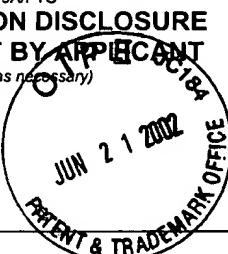


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 Sheet 1 of 3		Attorney Docket No: 01303.020US1					

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US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
TR	US-4412902	11/01/1983	Michikami, O., et al	204	192	06/18/1982
	US-4780424	10/25/1988	Holler, Mark A	437	29	09/28/1987
	US-5350738	09/27/1994	Hase, T., et al	505	473	11/27/1992
	US-5801401	09/01/1998	Forbes, L.	257	77	01/29/1997
	US-5852306	12/22/1998	Forbes, Leonard	257	315	01/29/1997
	US-5981350	11/09/1999	Geusic, J. E., et al	438	386	05/29/1998
TH	US-6025627	02/15/2000	Forbes, L., et al	257	321	05/29/1998

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T ²
TR		AFANAS'EV, V., et al., "Electron energy barriers between (100)Si and ultrathin stacks of SiO ₂ , Al ₂ O ₃ , and ZrO ₃ and ZrO ₂ insulators", <u>Applied Physics Letters</u> , 78(20), (2001), pp. 3073-3075				
		ARYA, S., "Conduction Properties of Thin Al ₂ O ₃ Films", <u>Thin Solid Films</u> , 91, (1982), pp. 363-374				
		DIPERT, BRIAN., "Flash Memory Goes Mainstream", <u>IEEE Spectrum</u> , 30, (October 1993), 48-52				
		ELDRIDGE, J., et al., "Analysis of Ultrathin Oxide Growth on Indium", <u>Thin Solid Films</u> , 12, (1972), pp. 447-451				
		ELDRIDGE, J., "Measurement of Tunnel Current Density in a Metal-Oxide-Metal System as a Function of Oxide Thickness", <u>Proc. 12th Intern. Conf. on Low Temperature Physics</u> , (1971), pp. 427-428				
		GREINER, J.G., "Josephson Tunneling Barriers by rf Sputter Etching in an Oxygen Plasma", <u>Journal of Applied Physics</u> , vol. 42, no. 12, (November 1971), 5151-5155				
		GREINER, J., "Oxidation of lead films by rf sputter etching in an oxygen plasma", <u>Journal of Applied Physics</u> , 45(1), (1974), pp. 32-37				
		GRIMBOLT, J., et al., "I. Interaction of Al Films with O ₂ at Low Pressures", <u>Journal of the Electrochemical Society</u> , 129(10), (1982), pp. 2366-2368				
		GRIMBOLT, J., et al., "II. Oxidation of Al Films", <u>Journal of Electrochem Soc.: Solid-State Science and Technology</u> , (1982), pp. 2369-2372				
		GUNDLACH, K., "Logarithmic Conductivity of Al-Al ₂ O ₃ -Al Tunneling Junctions Produced by Plasma and by Thermal Oxidation", <u>Surface Science</u> , 27, (1971), pp. 125-141				
		GUO, X., et al., "High Quality Ultra-thin (1.5 nm) TiO ₂ /Si ₃ N ₄ Gate Dielectric for				

EXAMINER

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DATE CONSIDERED

May 2002

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		<i>Complete if Known</i>	
		Application Number	09/943134
		Filing Date	August 30, 2001
		First Named Inventor	Forbes, Leonard
		Group Art Unit	92818
		Examiner Name	Unknown
Sheet 2 of 3		Attorney Docket No: 01303.020US1	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

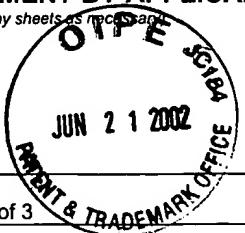
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
TH		Deep Sub-micron CMOS Technology", <u>IEDM Technical Digest</u> , (1999),pp. 137-140	
		HURYCH, Z., "Influence of Non-Uniform Thickness of Dielectric Layers on Capacitance and Tunnel Currents", <u>Solid-State Electronics</u> , vol. 9, (1966),967-979	
		ITOKAWA, H., et al. , "Determination of Bandgap and Energy Band Alignment for High-Dielectric-Constant Gate Insulators Using High-Resolution X-ray Photoelectron Spectroscopy", <u>Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials</u> , (1999),pp. 158-159	
		KIM, H., et al. , "Leakage current and electrical breakdown in metal-organic chemical vapor deposited TiO ₂ dielectrics on silicon substrates", <u>Applied Phys. Lett.</u> , 69(25), (1996),pp. 3860-3862	
		KUBASCHEWSKI, O., et al. , <u>Oxidation of Metals and Alloys</u> , Second Edition, Butterworths, London,(1962),pp. 1-3, 5,6, 8-12, 24, 36-39	
		KUBASCHEWSKI, O., "Oxidation of Metals and Alloys", Butterworths. London, (1962),53-63	
		KUKLI, K., et al. , "Development of Dielectric Properties of Niobium Oxide, Tantalum Oxide, and Aluminum Oxide Based Nanolayered Materials", <u>Journal of HTe Electrochemical Society</u> , 148(2), (2001),pp. F35-F41	
		KWO, J., et al. , "Properties of high k gate dielectrics Gd ₂ O ₃ and Y ₂ O ₃ for Si", <u>Journal of Applied Physics</u> , 89(7), (2001),pp. 3920-3927	
		LUAN, H., "High Technology Ta ₂ O ₅ Gate Dielectrics with Tox,eq<10A", <u>IEDM</u> , (1999),pp. 141-144	
		MA, Y., et al. , "Zirconium Oxide Based Gate Dielectrics with Dielectrics with equivalents Oxide Thickness of LEss Than 1.0 nm and Performance of Submicron MOSFET using a Nitride Gate Replacement Process", <u>IEDM - Technical Digest</u> , (1999),pp. 149-152	
		MASUOKA, F., "A 256K flash EEPROM using Triple Polysilicon Technology", <u>1985 IEEE International Solid-State Circuits Conference. Digest of Technical Papers</u> , (02/1985),168-169	
		MASUOKA, F., "A new Flash E2PROM Cell using Triple Polysilicon Technology", <u>International Electron Devices Meeting. Technical Digest</u> , (12/1984),464-467	
		MORI, S., "Reliable CVD Inter-Poly Dielectrics for Advanced E&EEPROM", <u>1985 Symposium on VLSI Technology. Digest of Technical Papers</u> , (1985),16-17	
		MULLER, H., "Electrical and Optical Properties of Sputtered In ₂ O ₃ Films", <u>Physica Status Solidi</u> , 27(2), (1968),pp.723-731	
		PASHLEY, RICHARD.D. , "Flash Memories: the best of two worlds", <u>IEEE Spectrum</u> , (12/1989), 30-33	
		POLLACK, S., "Tunneling Through Gaseous Oxidized Films of Al ₂ O ₃ ", <u>Transactions of the Metallurgical Society of AIME</u> , 233, (1965),pp. 497-501	

EXAMINER

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DATE CONSIDERED

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Substitute for form 1449A/PTO			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		<i>Complete if Known</i>	
(Use as many sheets as necessary)		Application Number	09/943134
		Filing Date	August 30, 2001
		First Named Inventor	Forbes, Leonard
		Group Art Unit	2818
		Examiner Name	Unknown
Sheet 3 of 3		Attorney Docket No: 01303.020US1	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
PF		QI, W., et al. , "MOSCAP and MOSFET characteristics using ZrO ₂ gate dielectric deposited directly on Si", <u>IEDM - Technical Digest</u> , (1999),pp. 145-148	
		ROBERTSON, J., "Band offsets of wide-band-gap oxides and implications for future electronic devices", <u>Journal Vac. Sci. Technol. B</u> , 18(3), (2000),pp. 1785-1791	
		ROBERTSON, J.,et al. , "Schottky barrier heights of tantalum oxide, barium strontium-titanate, lead titanate, and strontium bismuth tantalate", <u>Applied Physics Letters</u> , 74(8), (1999),pp. 1168-1170	
		SHI, Y.,et al. , "Tunneling Leakage Current in Ultrathin (<4 nm) Nitride/Oxide Stack Dielectrics", <u>IEEE Electron Device Letters</u> , 19(10), (1998),pp. 388-390	
		SIMMONS, J.,"Generalized Formula for the Electric Tunnel Effect between Similiar Electrodes Separated by a Thin Insulating Film", <u>Journal of Applied Physics</u> , 34(6), (1963),pp. 1793-1803	
		SWALIN, R.,"Equilibrium between Phases of Variable Composition", <u>Thermodynamics of Solids</u> , 2nd Edition, (1972),pp. 165-180	
		SZE, S., <u>Physics of Semiconductor Devices</u> , Second Edition, John Wiley & Sons, New York,(1981),pp. 553-556	
		YAN, J.,et al. , "Structural and electrical characterization of TiO ₂ grown from titanium tetrakis-isopropoxide (TTIP) and TTIP/H ₂ O ambients", <u>Journal Vac. Sci. Technol. B</u> , 14(3), (1996),pp. 1706-1711	

Note: Month where not specified is unknown

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